INFORMATION DISCLOSURE CITATION	ATTY. DOCKET NO. 160-399	SERIAL NO. 10/718,652
	APPLICANT NAKAMURA et al	
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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
MD		61-15385	01/1986	JAPAN			ABSTRACT	

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

*Examiner	[signature]	Date Considered	12-19-05

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APPLICANT	
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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ims		5,959,307	09/1999	NAKAMURA et al.	257	14	
ims		5,294,833	03/1994	SCHETZINA	257	741	
ims		5,670,798	09/1997	SCHETZINA	257	96	

FOREIGN PATENT DOCUMENTS

	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

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November 24, 2003	~~2828~~ 2822

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
IMS		5,793,054	08/1998	NIDO	257	18	

FOREIGN PATENT DOCUMENTS

		DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
IMS		JP 6-164085	06/1994	JAPAN			ABSTRACT	
IMS		JP 6-268259	09/1994	JAPAN			ABSTRACT	
IMS		JP 6-268257	09/1994	JAPAN			ABSTRACT	
IMS		JP 7-249795	09/1995	JAPAN			ABSTRACT	
IMS		JP 8-070139	03/1996	JAPAN			ABSTRACT	
IMS		JP 9-191160	07/1997	JAPAN			ABSTRACT	
IMS		JP 7-235729	09/1995	JAPAN			ABSTRACT	
IMS		JP 9-148247	06/1997	JAPAN			ABSTRACT	
IMS		JP 9-148678	06/1997	JAPAN			ABSTRACT	
IMS		JP 6-164055	06/1994	JAPAN			ABSTRACT	
IMS		JP 9-116225	05/1997	JAPAN			ABSTRACT	
IMS		JP 8-064910	03/1996	JAPAN			ABSTRACT	
IMS		JP 8-116128	05/1996	JAPAN			ABSTRACT	
IMS		JP 9-129925	05/1997	JAPAN			ABSTRACT	
IMS		JP 8-316581	11/1996	JAPAN			ABSTRACT	
IMS		EP 0 805 500	11/1997	EP			X	
IMS		JP 7-235729	09/1995	JAPAN			ABSTRACT	

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

IMS	AKASAKI et al., "Stimulated Emission by Current Injection from an AlGaN/GaN/GaInN Quantum Well Device," Jpn. J. Appl. Phys., Vol. 34 (1995), pp. L1517-L1519
IMS	NAKAMURA et al., "High-power InGaN Single-Quantum-Well-Structure Blue and Violet Light-Emitting Diodes." Appl. Phys. Lett. , Vol. 67, No. 13 (1995), pp. 1868-1870
IMS	NAKAMURA et al., "Candela-Class High-Brightness InGaN/AlGaN Double-Heterostructure Blue-Light-Emitting Diodes." Appl. Phys. Lett. Vol. 64, No. 13 (1994), pp. 1687-1689
	~~NARUKAWA et al.~~, "Recombination Dynamics of InGaN Quantum Wells by Time-Resolved Photoluminescence," Technical Report of the Institute of ~~Electronics, Information and Communication~~ Engineers (Oct. 1996) (Japan), pp. 81-88
IMS	WAKAHARA et al., "Growth of GaInN Alloy Layer and Its Composition Inhomogeneity," Technical Report of the Institute of Electronics, Information and Communication Engineers (Oct. 1996) (Japan), pp. 15-20
	NAKAMORI, T., "Unveiling the Structure of Pulse-Oscillate GaN Blue-Violet Semiconductor Laser." Nikkei Electronics (Jan. 1996) ~~(Japan) No. 653, pp. 13-15~~
	NAKAMURA, S., "Development of Blue Device in Final Stage," Electronics ~~(Feb. 1996)~~ (Japan), pp. 1-3
	NAKAMURA, S., "Latest Progress in Nitride-Based Blue/Green LED and Semiconductor Laser," International Forum "Blue Light-Emission" Project of Hoso-Bunka Foundation, Inc. (May 1996) (Japan) pp. 53-60.

*Examiner	John M. Smith	Date Considered	12-19-05

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INFORMATION DISCLOSURE CITATION

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160-399	10/229,067
APPLICANT	
Nakamura et al	
FILING DATE	**GROUP**
November 24, 2003	2822

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
IMS		5,684,309	11/1997	McIntosh et al	257	~~14~~ 191	
		4,862,471	8/1989	Pankove	372	45.01	
		5,646,953	7/1997	Naito et al	372	46.01	
		5,642,376	6/1997	Olbright et al	372	~~45~~ 99	
		5,475,700	12/1995	Iwata	372	45.01	
		5,247,533	9/1993	Okazaki et al	372	~~42~~ 45.01	
		5,959,307	9/1999	Nakamura et al	257	14	
		5,679,965	10/1997	Schetzina	257	103	
		5,412,226	5/1995	Rejman-Greene et al	257	21	
		5,751,013	5/1998	Kidoguchi et al	257	13	
		5,689,123	11/1997	Major et al	257	190	
		6,005,258	12/1999	Manabe et al	257	13	
IMS		5,247,533	9/1993	Okazaki et al	372	45.01	

FOREIGN PATENT DOCUMENTS

		DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
		0 675 552 A1	10/1995	Europe				
		6-21511	1/1994	Japan				
		3-290984	4/1990	Japan				
		4-218994	8/1992	Japan				
		7-074431	3/1995	Japan				X
		61-156788	7/1986	Japan				X
		08/290218	10/1996	Japan				X
		6-268257	6/1994	Japan				X
		6-177423	6/1994	Japan				X
		7-235723	9/1995	Japan				
		4-68579	3/1992	Japan				
		4-242985	8/1992	Japan				
		6-177423	6/1994	Japan				
		6-21511	1/1994	Japan				
		6-237039	8/1994	Japan				
		7-297447	11/1995	Japan				
		6-232451	8/1994	Japan			X	

OTHER DOCUMENTS (including Auth r, Titl , Date, Pertinent pages, tc.)

*Examiner	Peter M. Savage	Date Considered	12-19-05

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	160-399	10/229,067
	APPLICANT	
	Nakamura et al	
(Use several sheets if necessary)	FILING DATE	GROUP
	November 24, 2003	2822

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

		Narukawa et al Phys. Rev. B Vol. 55, No. 4, pp R1938-1941-1/97 Recombination dynamics of localized excitons in $In_{0.20}Ga_{0.80}N$-$In_{0.05}Ga_{0.95}N$ multiple quantum wells
		Narukawa et al Appl. Phys. Lett. 70 (8), pp 981-983, 2/1997 Role of self-formed InGaN quantum dots for exciton localization in the purple laser diode emitting at 420 nm
		Narukawa et al Appl. Phys. Lett., Vol. 74, No. 4 pp 558-560 1/99 Radioactive and nonradiative recombination processes in ultraviolet light-emitting diode composed of an $In_{0.02}Ga_{0.98}N$
		Nakamura et al Jpn. J. Appl. Phys., Vol. 35, pp L74-L76, Part 2, No. 1B, 1/96 InGaN-Based Multi-Quantum-Well Structure Laser Diodes
		Nakamura et al Jpn. J. Appl. Phys. , Vol. 35 (1996), pp L217-220, Part 2, No. 2B, 2/96 InGaN Multi-Quantum-Well Structure Laser Diodes with Cleved Mirror Cavity Facets:
		Nakamura et al Appl. Phys. Lett. 69 (11), pp. 1568-1570, 9/96 Optical gain and carrier lifetime of InGaN multi-quantum well structure laser diodes
		Jpn J. Appl. Phys. Vol. 34 (1995) pp. L1332-L1335, Part 2, No. 10B, 15 Oct. 1995, "Superbright Green InGaN Single-Quantum-WII-Structure Light-Emitting Diodes"
		Technical Report of IEICE, ED96-100, CPM96-78 (1996-10), pp. 15-21
		Technical Report of IEICE, ED96-110, CPM96-88 (1996-10), pp. 81-88
		Appl. Phys.Lett., 38 (11) June 1981 pp 835-837

*Examiner		Date Considered	12-19-05

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